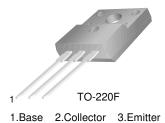


KSD1944

High Gain Power Transistor



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $\rm T_{C} = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	8	V
I _C	Collector Current	3	Α
P _C	Collector Current (T _C =25°C)	30	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 25 \text{mA}, I_{B} = 0$	60		V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 80V, I_{E} = 0$		100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 8V, I_{C} = 0$		10	μΑ
h _{FE}	DC Current Gain	$V_{CE} = 4V, I_{C} = 0.5A$	400	2000	
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 2A, I_B = 0.05A$		1.5	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = 2A, I_{B} = 0.05A$		1	V

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Typical Characteristics

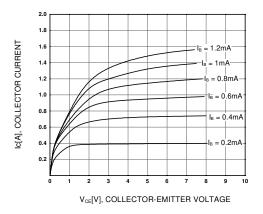


Figure 1. Static Characteristic

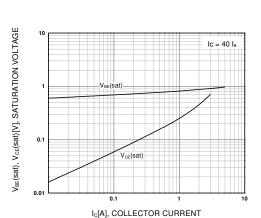


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

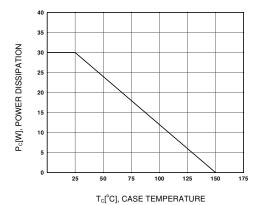


Figure 5. Power Derating

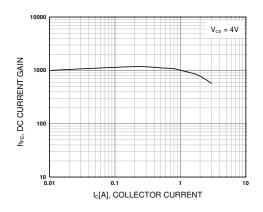


Figure 2. DC current Gain

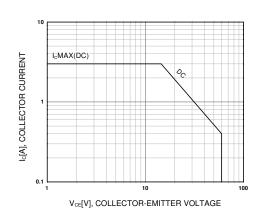


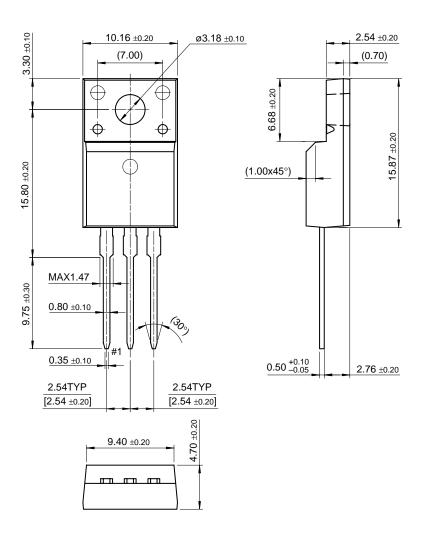
Figure 4. Safe Operating Area

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Package Demensions

TO-220F



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